

FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. P27127		Application No. 10/707,840	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)				Applicant Huilong ZHU et al.			
				Filing Date January 16, 2004		Group 2811 2818	
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EXAMINER /Dao Nguyen/				DATE CONSIDERED 01/08/2007			
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